

ABSTRACT

HIGH-PRESSURE SUBSTRATE PROCESSING APPARATUS

Provided is a high-pressure substrate processing apparatus including: an inner chamber accommodating a substrate to be processed and a reaction gas forming a first pressure higher than atmospheric pressure; an outer chamber including an outer housing accommodating the inner chamber, and an outer door defining a protective space for accommodating a protective gas forming a second pressure set in relation to the first pressure together with the outer housing and the inner chamber, one of the outer housing and the outer door having a mounting groove formed in its corresponding surface facing the other one of the outer housing and the outer door; and a sealing unit accommodated in the mounting groove and in contact with the other one to isolate the protective gas from external air, and a vent channel extending along an intersecting direction that intersects the corresponding surface to discharge the protective gas flowing into the mounting groove.

FIG. 2